

Schottky Barrier Rectifier

MBR60200PT

FEATURES

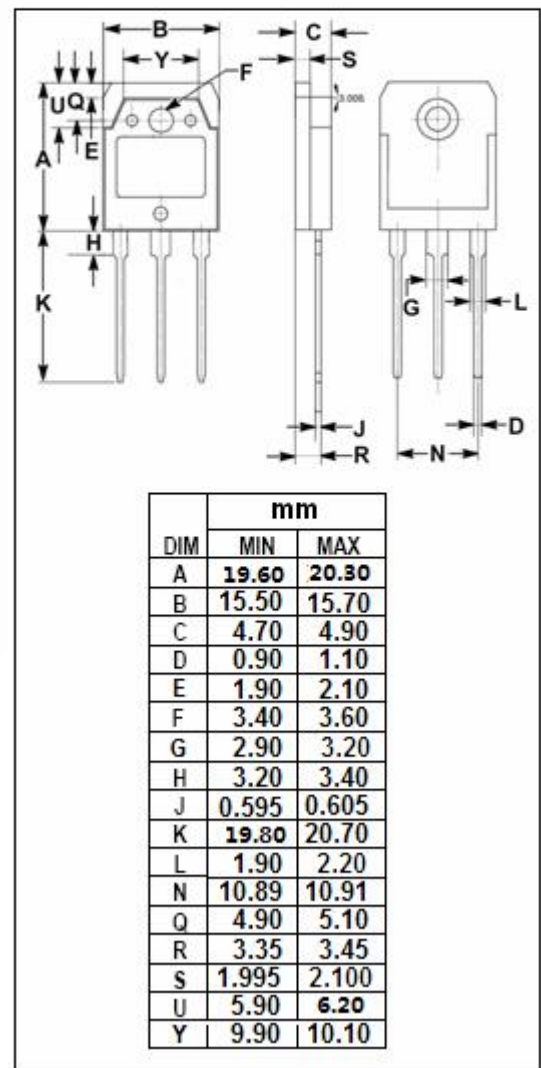
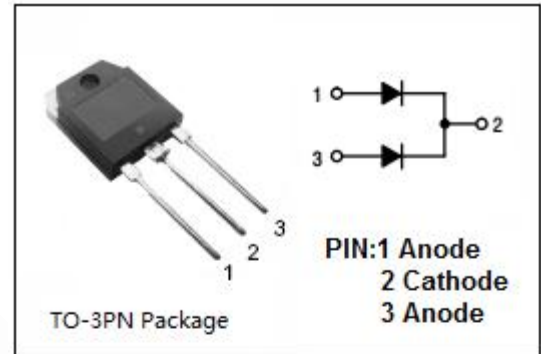
- Plastic material used carriers Unerwriter Laboratory
- Metal silicon rectifier, majonty carrier conduction
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Surge Capability,High Current Capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For use in low voltage ,high frequency inverters,free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	200	V
V _{R(RMS)}	RMS Reverse Voltag	140	V
I _{F(AV)}	Average Rectified Forward Current	60	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	400	A
I _{RRM}	Peak Repetitive Reverse Surge Current (20 μ s, 1.0kHz)	1.0	A
T _J	Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-65~175	°C
dv/dt	Voltage Rate of Change (Rated V _R)	1,000	V/ μ s



Schottky Barrier Rectifier**MBR60200PT****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.5	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s, Duty Cycle \leq 1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 30A ; T_c = 25^{\circ}C$	0.9	V
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}; T_c = 25^{\circ}C$	0.05	mA
		$V_R = V_{RWM}; T_c = 100^{\circ}C$	10.0	